

# OPA7735H

High Speed

## Infrared LED Chip

GaAlAs /GaAs

### 1. Material

Substrate GaAs (N Type)  
Epitaxial Layer GaAlAs (N/P Type)

### 2. Electrode

N (Cathode) Side Gold Alloy  
P (Anode) Side Gold Alloy

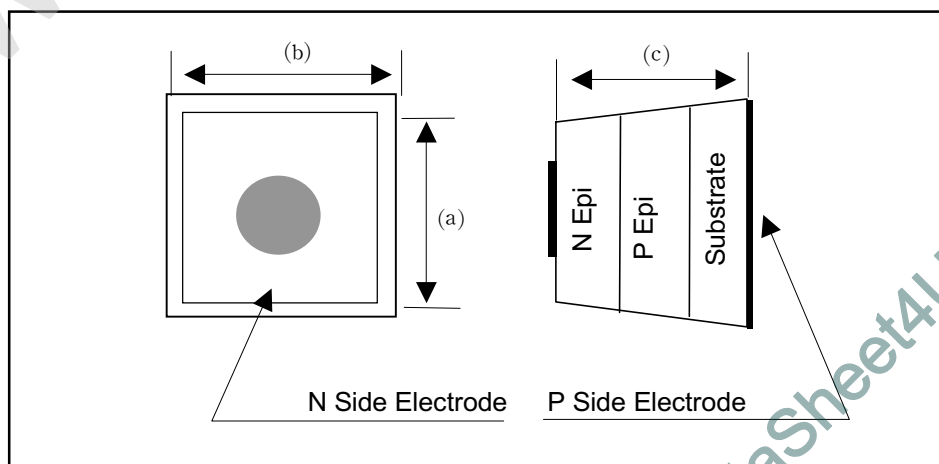
### 3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$		1.7	2.0	V	$I_F=20\text{mA}$
	$V_{F(2)}$		2.0	2.5	V	$I_F=100\text{mA}$
Reverse Voltage	$V_R$	5.0			V	$I_R=10\mu\text{A}$
Power	$P_{O(1)}$		1		mW	$I_F=20\text{mA}$
	$P_{O(2)}$		4		mW	$I_F=100\text{mA}$
Wavelength	$\lambda_P$		770		nm	$I_F=20\text{mA}$
	$\Delta\lambda$		30		nm	$I_F=20\text{mA}$
Rise Time	$t_r$		40		ns	$I_F=50\text{mA}$

Note : Assembled into TO-18 Header without resin coating.

### 4. Mechanical Data

- (a) Emission Area ----- 12mil × 12mil
- (b) Bottom Area ----- 14mil × 14mil
- (c) Chip Thickness ----- 10mil



Knowledge\*on Inc.

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513-37 Eoyang-dong, Iksan, 570-210, Korea. Tel: +82-63-839-1111. Fax: +82-63-835-8259

